HD74HCT374/HD74HCT534

Octal D-type Flip-Flops (with 3-state outputs)/
Octal D-type Flip-Flops (with inverted 3-state outputs)

HITACHI

Description

These device are positive edge triggered flip-flops. The difference between HD74HCT374 and HD74HCT534 is only that the former is a true outputs and the latter is a false outputs. Data at the D inputs, meeting the setup and hold time requirements, are transferred to the Q outputs on positive going transitions of the clock (CK) input. When a high logic level is applied to the output control (OC) input, all outputs go to a high impedance state, regardless of what signals are present at the other inputs and the state of the storage elements.

Features

- LSTTL Output Logic Level Compatibility as well as CMOS Output Compatibility
- High Speed Operation: t_{pd} (Clock to Q) = 15 ns typ (C_L = 50 pF)
- High Output Current: Fanout of 15 LSTTL Loads
- Wide Operating Voltage: V_{CC} = 4.5 to 5.5 V
- Low Input Current: 1 µA max
- Low Quiescent Supply Current: I_{CC} (static) = 4 µA max (Ta = 25°C)

Function Table

			HD74HCT374	HD74HCT534
Output Control	**Clock**	**D**	**Q**	**$\overline{Q}$**
L	⎍	H	H	L
L	⎍	L	L	H
L	L	X	No change	No change
H	X	X	Z	Z

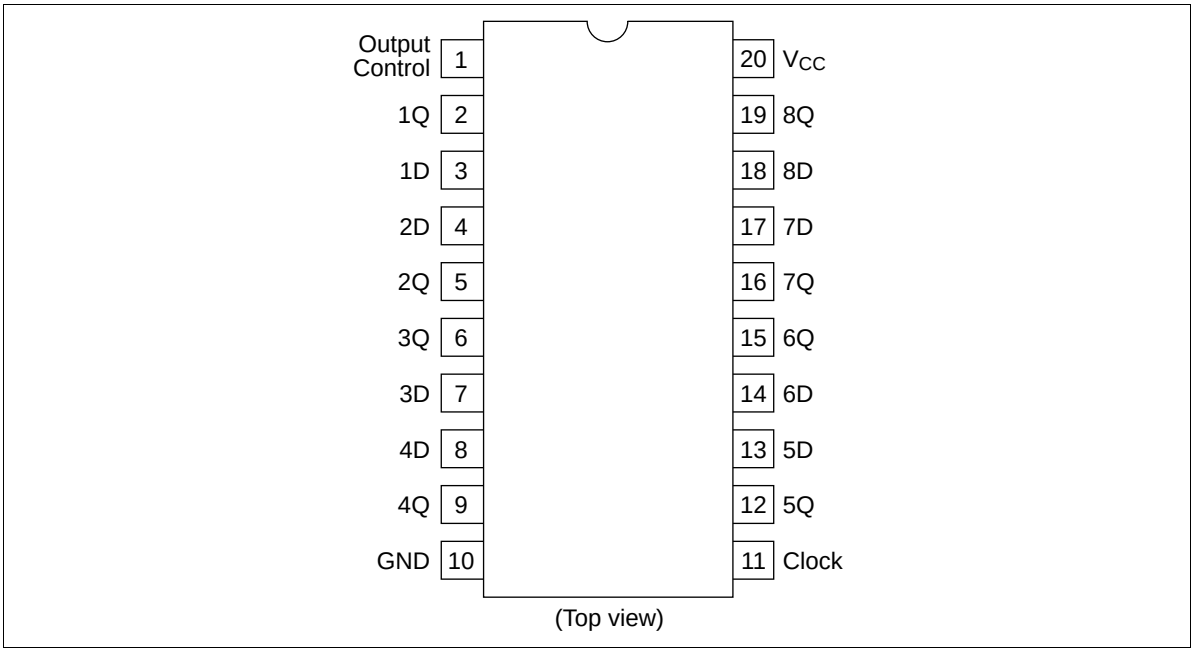
X : Irrelevant

Z : Off (high-impedance) state of a 3-state output.

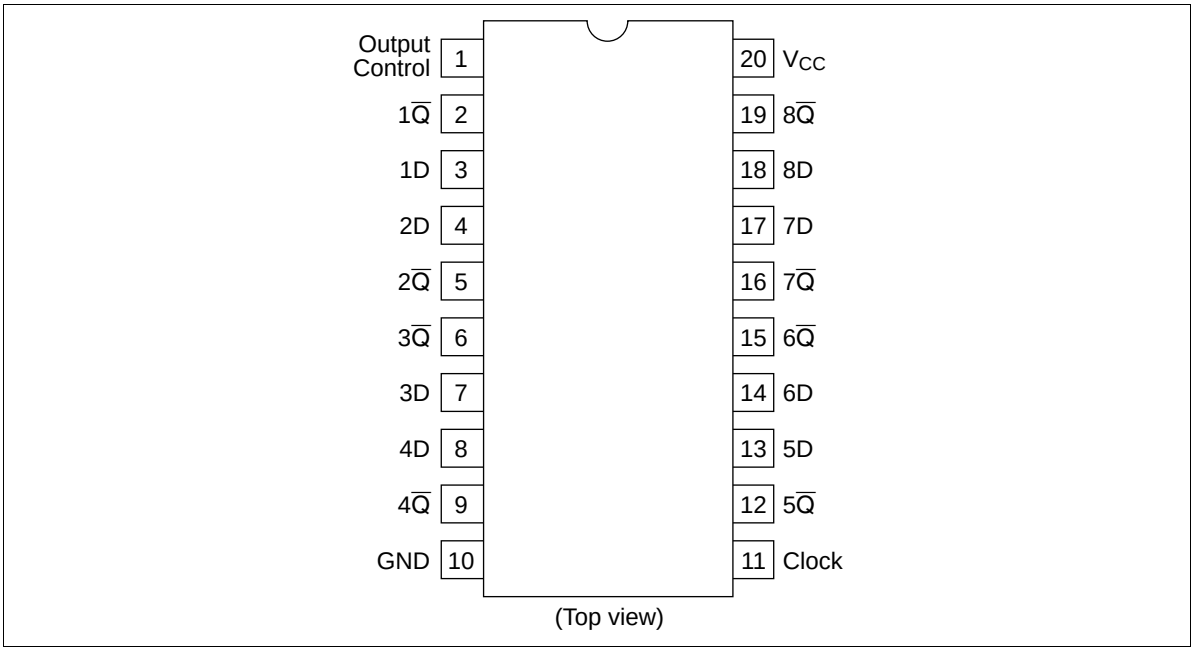
Hitachi semiconductor

Pin Arrangement

HD74HCT374

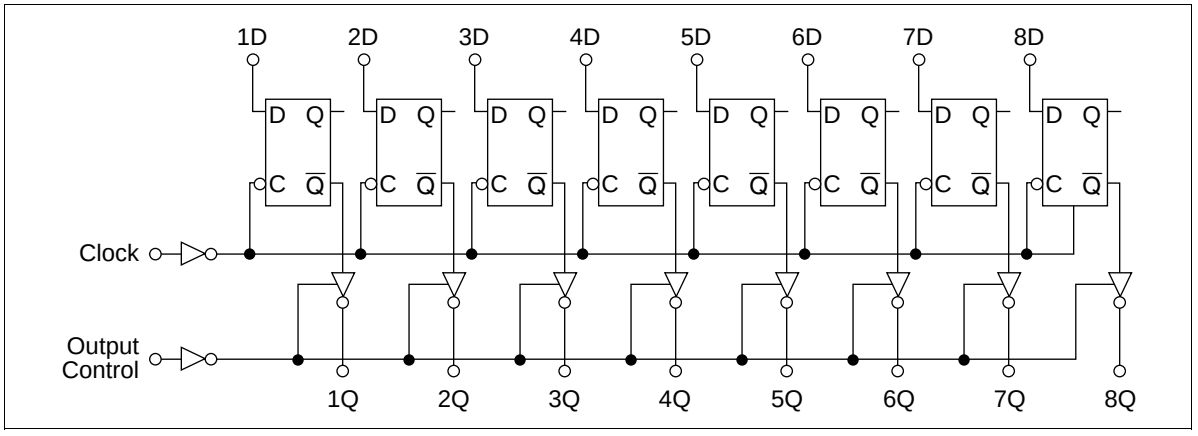


HD74HCT534

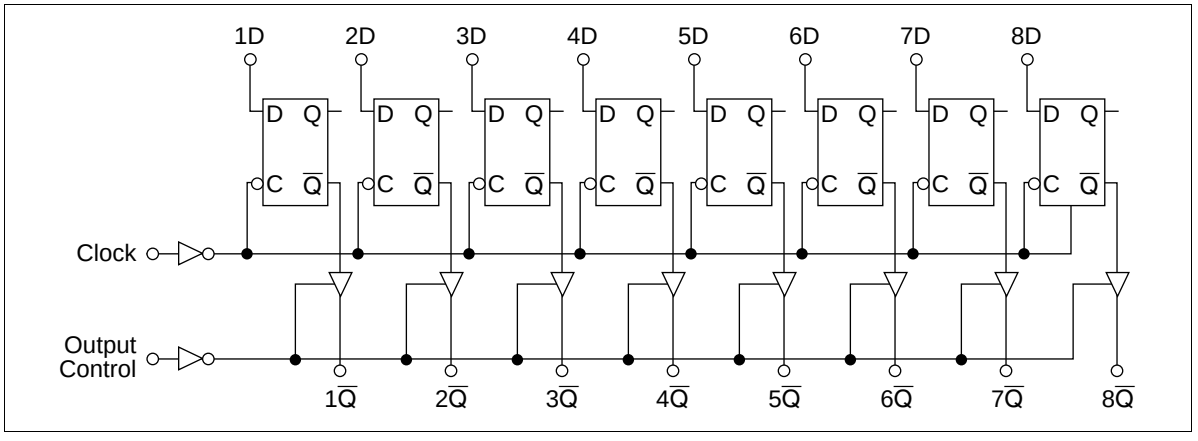


Block Diagram

HD74HCT374



HD74HCT534



Absolute Maximum Ratings

Item	Symbol	Rating	Unit
Supply voltage range	V_{CC}	–0.5 to +7.0	V
Input voltage	V_{IN}	–0.5 to V_{CC} + 0.5	V
Output voltage	V_{OUT}	–0.5 to V_{CC} + 0.5	V
DC current drain per pin	I_{OUT}	±35	mA
DC current drain per V_{CC}, GND	I_{CC}, I_{GND}	±75	mA
DC input diode current	I_{IK}	±20	mA
DC output diode current	I_{OK}	±20	mA
Power dissipation per package	P_T	500	mW
Storage temperature	Tstg	–65 to +150	°C

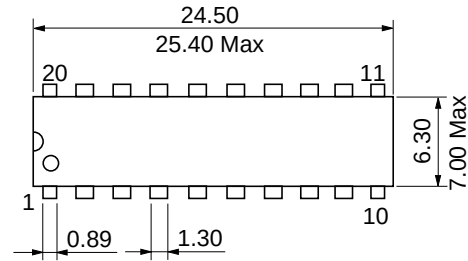
DC Characteristics

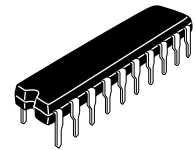
		Ta = 25°C			Ta = –40 to +85°C			Test Conditions		
Item	Symbol	Min	Typ	Max	Min	Max	Unit	V_{cc} (V)		
Input voltage	V_{IH}	2.0	—	—	2.0	—	V	4.5 to 5.5		
	V_{IL}	—	—	0.8	—	0.8	V	4.5 to 5.5		
Output voltage	V_{OH}	4.4	—	—	4.4	—	V	4.5	Vin = V_{IH} or V_{IL}	I_{OH} = –20 µA
		4.18	—	—	4.13	—		4.5		I_{OH} = –6 mA
	V_{OL}	—	—	0.1	—	0.1	V	4.5	Vin = V_{IH} or V_{IL}	I_{OL} = 20 µA
		—	—	0.26	—	0.33		4.5		I_{OL} = 6 mA
Off-state output current	I_{OZ}	—	—	±0.5	—	±5.0	µA	5.5	Vin = V_{IH} or V_{IL}, Vout = V_{CC} or GND	
Input current	Iin	—	—	±0.1	—	±1.0	µA	5.5	Vin = V_{CC} or GND	
Quiescent current	I_{CC}	—	—	4.0	—	40	µA	5.5	Vin = V_{CC} or GND, Iout = 0 µA	

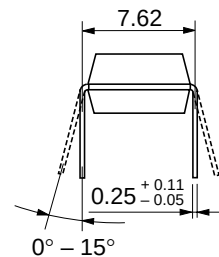
AC Characteristics (C_L = 50 pF, Input $t_r = t_f$ = 6 ns)

		Ta = 25°C			Ta = –40 to +85°C			Test Conditions	
Item	**Symbol**	**Min**	**Typ**	**Max**	**Min**	**Max**	**Unit**	**V_{cc} (V)**	
Maximum clock frequency	f_{max}	—	—	30	—	24	MHz	4.5	
Propagation delay	t_{PLH}	—	12	28	—	35	ns	4.5	
time	t_{PHL}	—	15	28	—	35		4.5	
Output enable	t_{ZL}	—	16	30	—	38	ns	4.5	
time	t_{ZH}	—	15	30	—	38		4.5	
Output disable	t_{LZ}	—	13	30	—	38	ns	4.5	
time	t_{HZ}	—	16	30	—	38		4.5	
Setup time	t_{su}	20	2	—	25	—	ns	4.5	Data to clock
Hold time	t_h	5	0	—	6	—	ns	4.5	Clock to data
Pulse width	t_w	16	5	—	20	—	ns	4.5	Clock, output control
Output rise/fall time	t_{TLH} t_{THL}	—	4	12	—	15	ns	4.5	
Input capacitance	Cin	—	5	10	—	10	pF	—	

Unit: mm

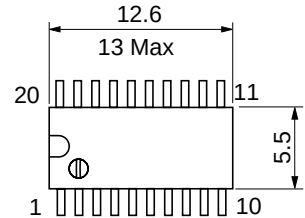


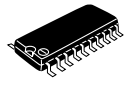


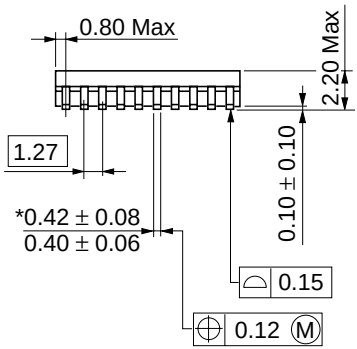


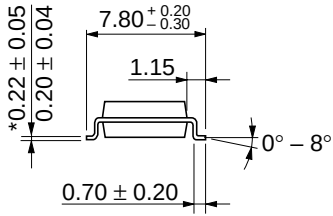
Hitachi Code	DP-20N
JEDEC	—
EIAJ	Conforms
Weight (reference value)	1.26 g

Unit: mm





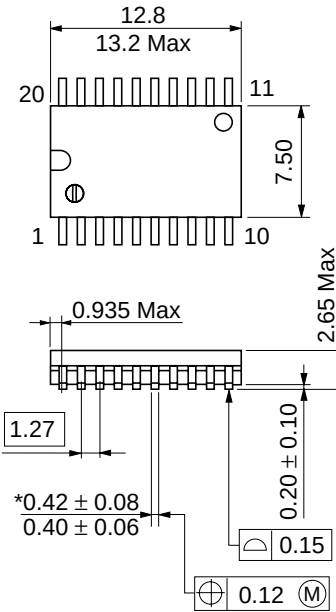


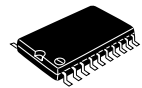


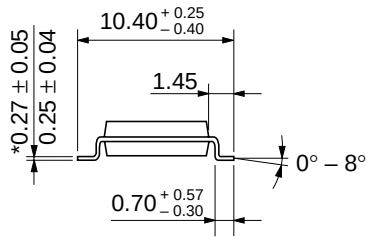
*Dimension including the plating thickness
Base material dimension

Hitachi Code	FP-20DA
JEDEC	—
EIAJ	Conforms
Weight (reference value)	0.31 g

Unit: mm



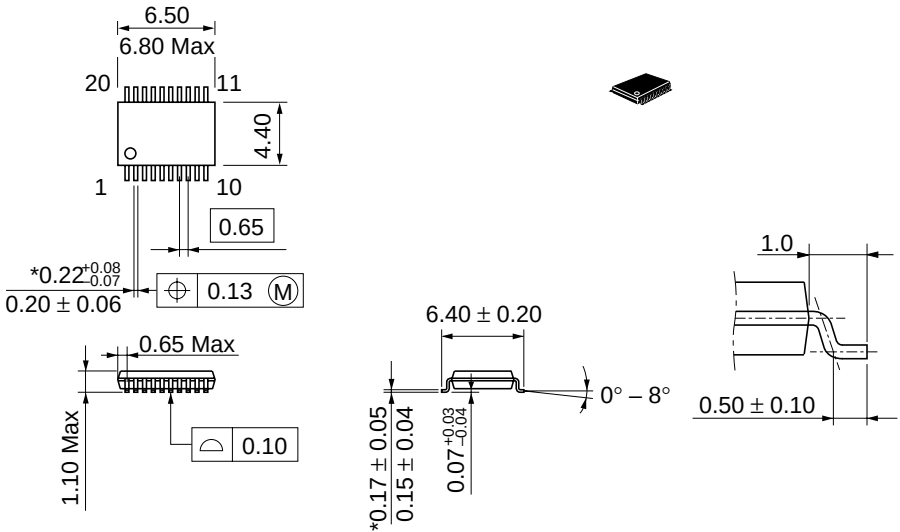




*Dimension including the plating thickness
Base material dimension

Hitachi Code	FP-20DB
JEDEC	Conforms
EIAJ	—
Weight (reference value)	0.52 g

Unit: mm



Hitachi Code	TTP-20DA
JEDEC	—
EIAJ	—
Weight (reference value)	0.07 g

*Dimension including the plating thickness
Base material dimension

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